

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

NPN Epitaxial Planar Silicon Transistor

2SC5347A — High-Frequency Semi-Power Output Stage, **Low-Noise Medium Output Amplifier Applications**

Features

· High-frequency medium output amplification

(VCE=5V, IC=50mA)

: fT=4.7GHz typ (f=1GHz).

 $| S21e |^2 = 8dB \text{ typ (}f = 1GHz).$

: NF=1.8dB typ (f=1GHz).

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		20	V
Collector-to-Emitter Voltage	VCEO		12	V
Emitter-to-Base Voltage	VEBO		2	V
Collector Current	IC		150	mA
Collector Dissipation	PC	When mounted on ceramic substrate (900mm ² X0.8mm)	1.3	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

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Electrical Characteristics at Ta=25°C

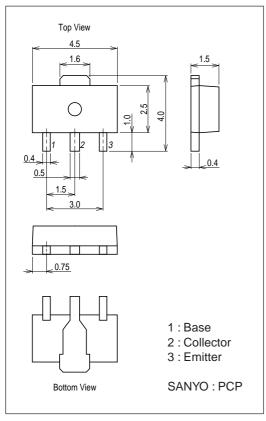
Parameter	Symbol	Conditions	Ratings			Unit
r arameter	Symbol	Conditions	min	typ	max	Offic
Collector Cutoff Current	ICBO	VCB=10V, IE=0A			1.0	μА
Emitter Cutoff Current	IEBO	V _{EB} =1V, I _C =0A			10	μΑ
DC Current Gain	hFE	V _{CE} =5V, I _C =50mA	60*		270*	
Gain-Bandwidth Product	fT	VCE=5V, IC=50mA	3	4.7		GHz
Output Capacitance	Cob	V _{CB} =10V, f=1MHz		1.3	2.0	pF
Reverse Transfer Capacitance	Cre	V _{CB} =10V, f=1MHz		0.9		pF
Forward Transfer Gain	S21e ²	V _{CE} =5V, I _C =50mA, f=1GHz	6	8		dB
Noise Figure	NF	V _{CE} =5V, I _C =50mA, f=1GHz		1.8	3.0	dB

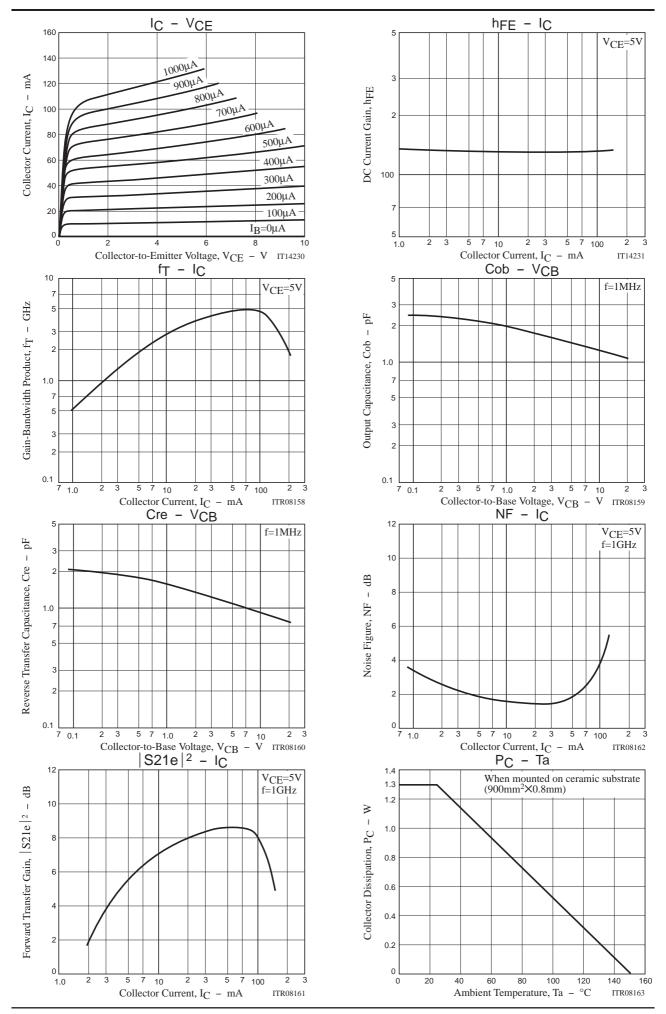
* : The 2SC5347A is classified by 50mA hFE as follows :

Marking	CZ	CZ	CZ
Rank	D	Е	F
hFE	60 to 120	90 to 180	135 to 270

Package Dimensions

unit : mm (typ) 7007A-004



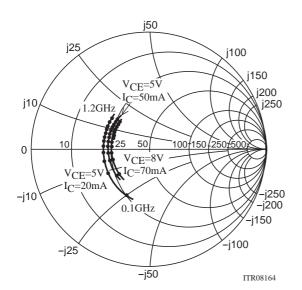


2SC5347A

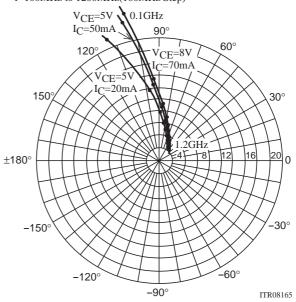
S Parameter

S11e

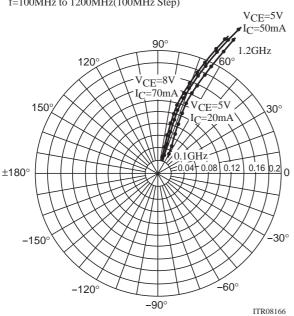
f=100MHz to 1200MHz(100MHz Step)



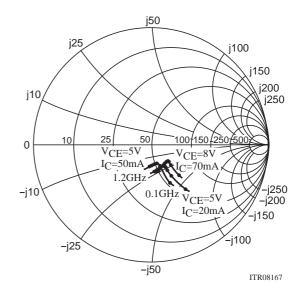
S21e f=100MHz to 1200MHz(100MHz Step)



S12e f=100MHz to 1200MHz(100MHz Step)



S22e f=100MHz to 1200MHz(100MHz Step)



2SC5347A

S Parameters (Common emitter)

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Freq(MHz)	$ S_{11} $	∠S ₁₁	S ₂₁	∠S ₂₁	S ₁₂	∠S ₁₂	S ₂₂	∠S ₂₂
100	0.358	-141.0	24.005	105.9	0.027	68.4	0.342	-63.0
200	0.354	-165.7	12.593	93.3	0.047	72.7	0.205	-68.4
300	0.355	-176.8	8.532	86.8	0.068	74.1	0.166	-69.7
400	0.359	174.9	6.428	81.9	0.089	73.7	0.149	-72.3
500	0.359	169.3	5.293	77.6	0.110	72.8	0.145	-75.3
600	0.362	163.9	4.360	73.5	0.130	71.7	0.143	-78.6
700	0.366	158.5	3.774	69.9	0.151	70.2	0.147	-82.1
800	0.364	153.5	3.334	66.4	0.171	68.6	0.151	-85.6
900	0.368	149.8	2.995	62.9	0.191	66.7	0.158	-90.1
1000	0.370	145.3	2.725	59.4	0.210	65.1	0.166	-92.3
1100	0.373	141.5	2.494	56.5	0.230	63.0	0.170	-95.1
1200	0.377	137.6	2.307	53.0	0.248	61.4	0.177	-97.8

 $V_{CE}=5V$, $I_{C}=20mA$, $Z_{O}=50\Omega$

Freq(MHz)	S ₁₁	∠S ₁₁	S ₂₁	∠S ₂₁	S ₁₂	∠S ₁₂	S ₂₂	∠S ₂₂
100	0.445	-115.4	21.095	113.8	0.032	59.7	0.479	-52.4
200	0.400	-149.6	11.567	97.4	0.049	63.4	0.300	-58.0
300	0.394	-165.7	7.917	89.3	0.066	67.0	0.242	-58.8
400	0.391	-176.5	5.974	82.5	0.085	68.5	0.214	-60.0
500	0.391	176.7	4.845	78.4	0.103	68.8	0.203	-62.2
600	0.392	169.4	4.065	73.9	0.122	68.6	0.199	-64.7
700	0.393	163.8	3.522	70.0	0.141	67.8	0.198	-67.9
800	0.394	158.4	3.114	66.4	0.159	67.1	0.201	-71.2
900	0.396	154.1	2.798	62.5	0.178	65.7	0.204	-74.7
1000	0.399	149.3	2.548	58.9	0.196	64.5	0.212	-78.1
1100	0.403	144.9	2.333	55.5	0.215	62.9	0.218	-81.4
1200	0.408	141.0	2.158	51.8	0.233	61.8	0.224	-84.1

 V_{CE} =8V, I_{C} =70mA, Z_{O} =50 Ω

Freq(MHz)	S ₁₁	∠S ₁₁	S ₂₁	∠S ₂₁	S ₁₂	∠S ₁₂	S ₂₂	∠S ₂₂
100	0.328	-141.2	25.505	105.1	0.024	70.5	0.348	-50.8
200	0.323	-165.7	13.334	93.0	0.043	75.0	0.233	-48.9
300	0.323	-176.6	9.025	86.7	0.062	75.8	0.204	-47.0
400	0.326	175.1	6.819	81.8	0.081	75.5	0.191	-48.0
500	0.325	169.5	5.481	77.8	0.100	74.5	0.187	-50.5
600	0.328	163.6	4.612	73.7	0.119	73.4	0.185	-53.6
700	0.330	158.4	3.980	70.2	0.139	71.8	0.188	-57.3
800	0.333	153.5	3.524	66.7	0.157	70.4	0.191	-60.9
900	0.335	150.0	3.148	63.3	0.177	68.5	0.198	-65.1
1000	0.341	144.7	2.866	60.0	0.194	67.1	0.204	-69.0
1100	0.345	141.2	2.629	57.0	0.213	65.1	0.208	-72.1
1200	0.348	138.0	2.424	53.4	0.230	62.6	0.215	-75.3

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